400V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 400V
- I_C = 300mA High Continuous Current
- Excellent h_{FE} Characteristics up to 100mA
- Low Saturation Voltage $V_{CE(sat)}$ < 200mV @ 20mA
- Complementary PNP Type: FZT558
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

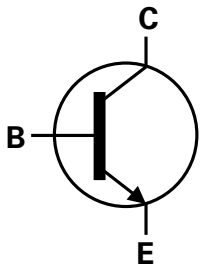
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (Approximate)

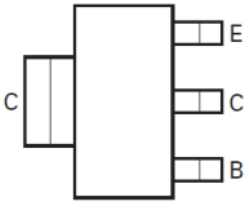
SOT223 (Type DN)



Top View



Device Symbol



Top View
Pinout

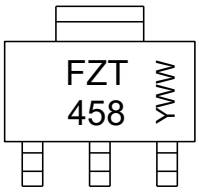
Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
FZT458TA	SOT223 (Type DN)	FZT458	7	12	1,000	Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223 (Type DN)



FZT 458 = Product Type Marking Code
YWW = Date Code Marking
Y or $\overline{Y}$ = Last Digit of Year (ex: 6 = 2026)
WW or $\overline{WW}$ = Week Code (01 to 53)

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	300	mA
Base Current	I_B	200	mA
Peak Pulse Current	I_{CM}	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	2	W
	(Note 6)		3	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	62.5	°C/W
	(Note 6)		41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)		$R_{\theta JL}$	19.41	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
6. Same as Note 5, except the device is mounted on 50mm x 50mm single-sided 2oz weight copper.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specifications JESD22-A114 and JESD22-A115.

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Thermal Characteristics and Derating Characteristics

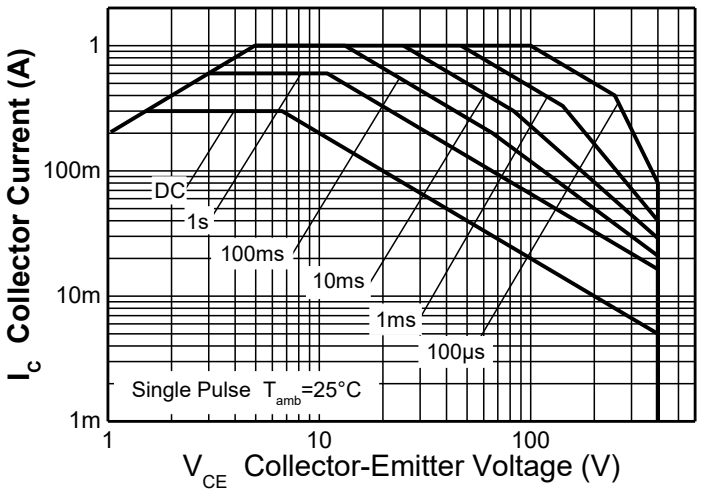


Fig. 1 Safe Operating Area

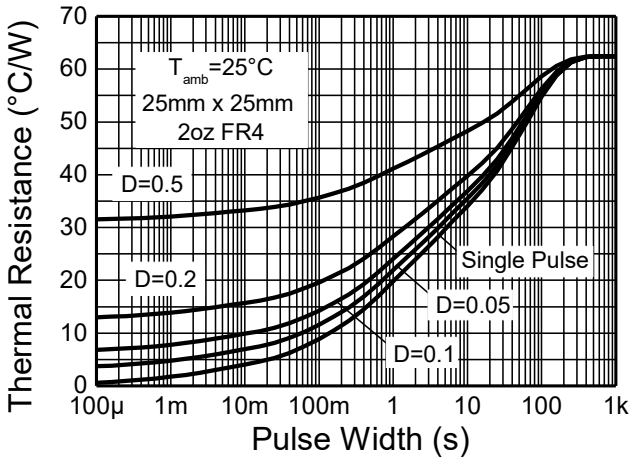


Fig. 2 Transient Thermal Impedance

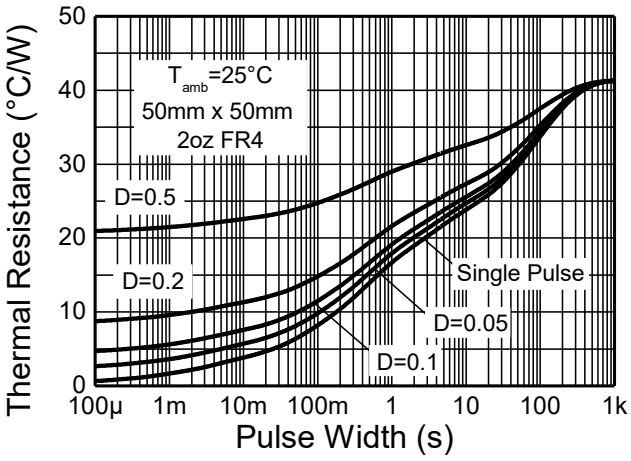


Fig. 3 Transient Thermal Impedance

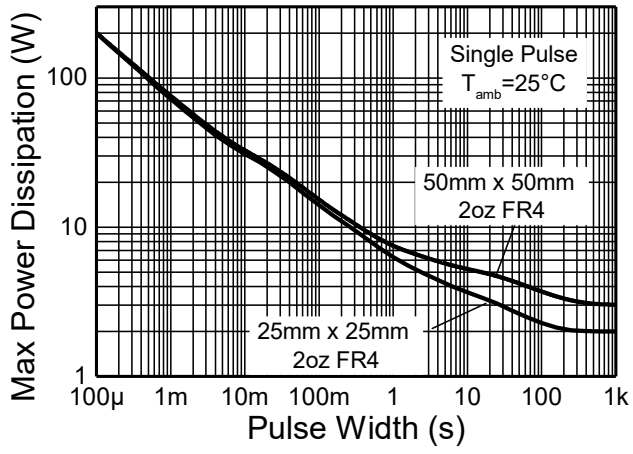


Fig. 4 Pulse Power Dissipation

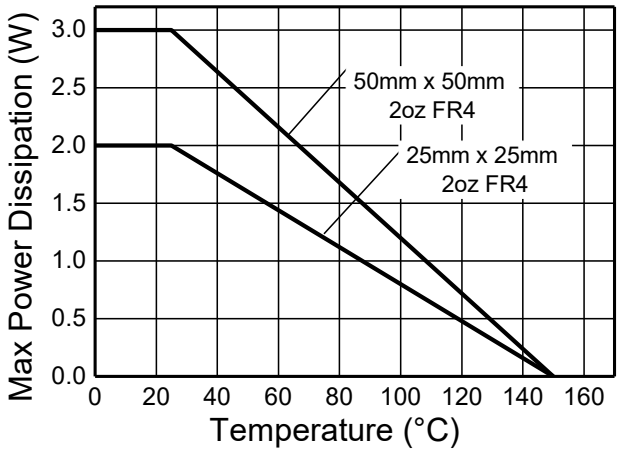


Fig. 5 Derating Curve

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	400	—	—	V	I_C = 100µA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	400	—	—	V	I_C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	I_E = 100µA
Collector Cutoff Current	I_{CBO}	—	—	100	nA	V_{CB} = 320V
Collector Cutoff Current	I_{CES}	—	—	100	nA	V_{CE} = 320V
Emitter Cutoff Current	I_{EBO}	—	—	100	nA	V_{EB} = 4V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	— —	— —	0.2 0.5	V	I_C = 20mA, I_B = 2mA I_C = 50mA, I_B = 6mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	—	0.9	V	I_C = 50mA, I_B = 5mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	—	—	0.9	V	I_C = 50mA, V_{CE} = 10V
DC Current Gain (Note 9)	h_{FE}	100 100 15	— — —	— 300 —	—	I_C = 1mA, V_{CE} = 10V I_C = 50mA, V_{CE} = 10V I_C = 100mA, V_{CE} = 10V
Current Gain-Bandwidth Product (Note 9)	f_T	50	—	—	MHz	V_{CE} = 20V, I_C = 10mA f = 20MHz
Output Capacitance (Note 9)	C_{obo}	—	—	5	pF	V_{CB} = 20V, f = 1MHz
Switching Time	t_{on}	—	135	—	ns	I_C = 50mA, V_{CC} = 100V I_{B1} = 5mA, I_{B2} = -10mA
	t_{off}	—	2260	—		

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

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Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

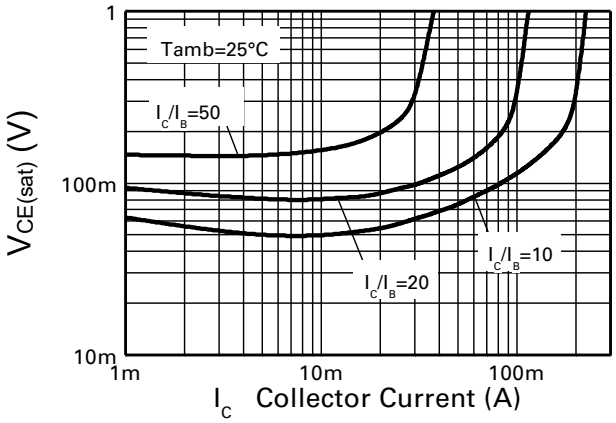


Fig. 6 $V_{CE(sat)}$ v I_C

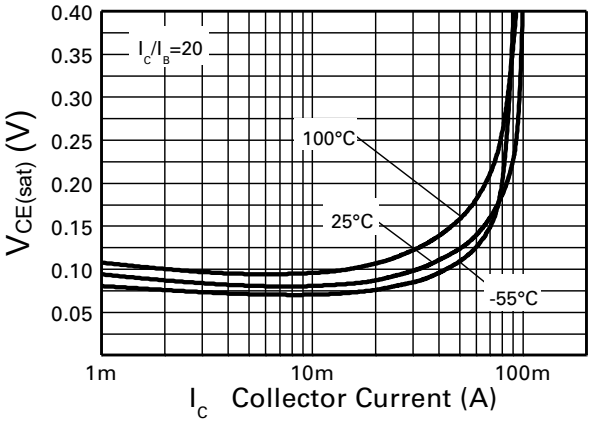


Fig. 7 $V_{CE(sat)}$ v I_C

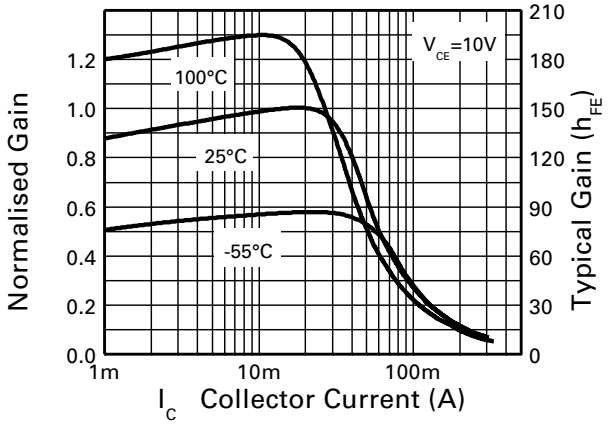


Fig. 8 hFE v I_C

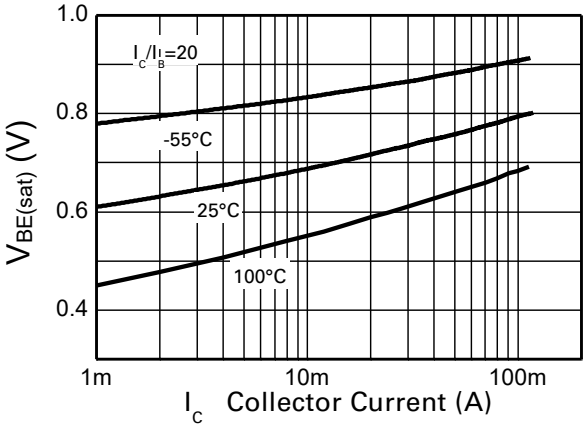


Fig. 9 $V_{BE(sat)}$ v I_C

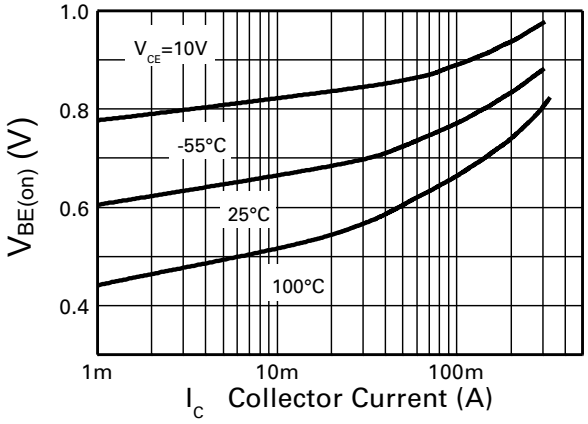


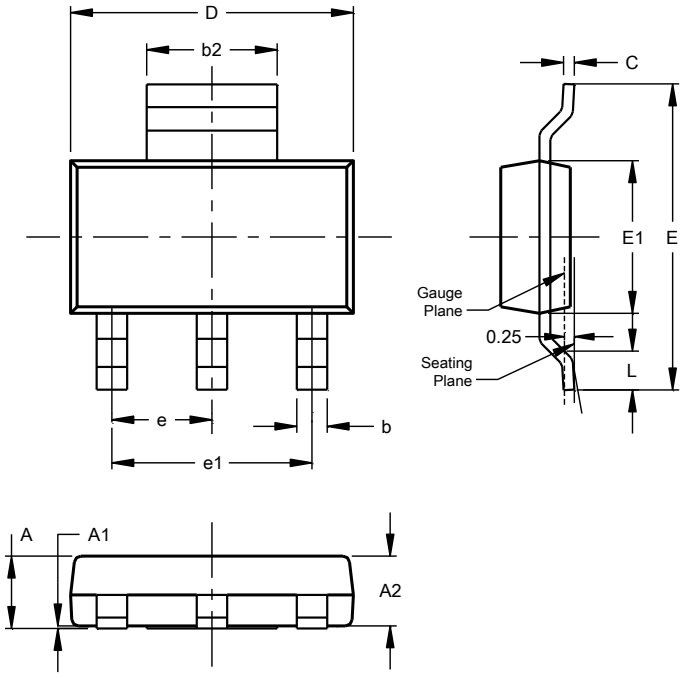
Fig. 10 $V_{BE(on)}$ v I_C

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

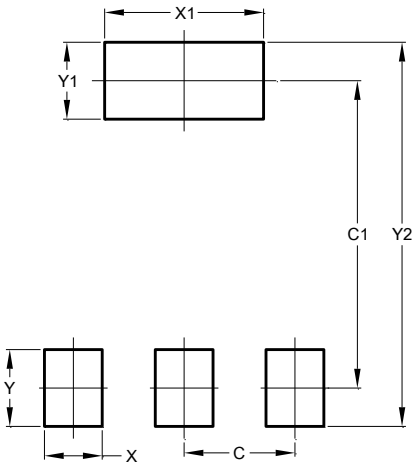


SOT223 (Type DN)			
Dim	**Min**	**Max**	**Typ**
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: 10. For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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